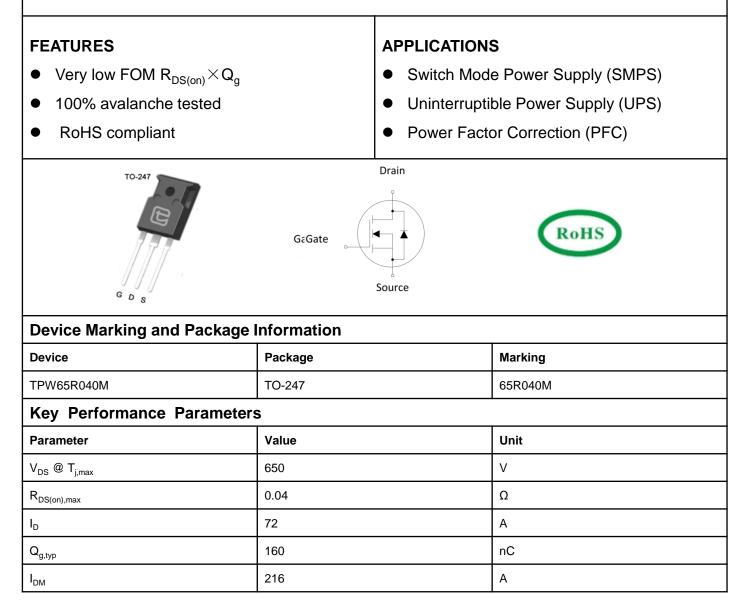


# **650V Super-Junction Power MOSFET**

#### DESCRIPTION

#### 650V super-junction Power MOSFET

Super-junction power MOSFET is a revolutionary technology for high voltage power MOSFETs, designed according to the SJ principle. The SJ MOSFET is a price-performance optimized product enabling to target cost sensitive applications in Consumer and Lighting markets, designed by Wuxi Unigroup Microelectronics Company.



<b>Absolute Maximum Ratings</b> $T_c = 25^{\circ}C$ , unless otherwise noted					
Parameter		Symbol	Value	Unit	
Drain-Source Voltage (V <sub>GS</sub> = 0V)		V <sub>DSS</sub>	650	V	
Continuous Drain Current	T <sub>C</sub> = 25°C	l <sub>D</sub>	72	А	
	TC = 100°C		43.2		
Pulsed Drain Current (note1)		I <sub>DM</sub>	216	А	
Gate-Source Voltage		V <sub>GSS</sub>	±30	V	
Single Pulse Avalanche Energy (note2)		E <sub>AS</sub>	2185	mJ	
Repetitive Avalanche Energy (note2)		E <sub>AR</sub>	3.31	mJ	
Avalanche Current		I <sub>AR</sub>	13.7	A	
MOSFET dv/dt ruggedness, V <sub>DS</sub> = 0480V		dv/dt	50	V/ns	
Power Dissipation		P <sub>D</sub>	500	W	
Continuous Body Diode Current		۱ <sub>s</sub>	61		
Pulsed Diode Forward Current (note1)		I <sub>SM</sub>	216	A	
Reverse diode dv/dt (note3)		dv/dt	15	V/ns	
Maximum diode commutation speed (note3)		di <sub>f</sub> /dt	500	A/us	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55~+150	°C	

Thermal Resistance				
Parameter	Symbol	Value	Unit	
Thermal Resistance, Junction-to-Case	R <sub>thJC</sub>	0.25 °C/W		
Thermal Resistance, Junction-to-Ambient	R <sub>thJA</sub>	62	~C/W	



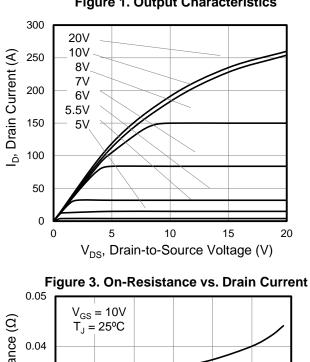
Devenueter			Value				
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static	•						
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	$V_{GS} = 0V, I_{D} = 250\mu A$	650			V	
Zero Gate Voltage Drain Current		$V_{DS} = 650V, V_{GS} = 0V, T_{J} = 25^{\circ}C$			1	μA	
	I <sub>DSS</sub>	$V_{DS} = 650V, V_{GS} = 0V, T_{J} = 150^{\circ}C$			100		
Gate-Source Leakage	I <sub>GSS</sub>	$V_{GS} = \pm 30 V$			±100	nA	
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_D = 250 \mu A$	2.5		4.5	V	
Drain-Source On-Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10V, I <sub>D</sub> = 25A		0.035	0.04	Ω	
Gate resistance	R <sub>G</sub>	f = 1.0MHz open drain		0.3		Ω	
Dynamic							
Input Capacitance	C <sub>iss</sub>			7565		pF	
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0V,$ $V_{DS} = 100V,$		268			
Reverse Transfer Capacitance	C <sub>rss</sub>	f = 1.0MHz		3.3			
Total Gate Charge	Qg			160		nC	
Gate-Source Charge	Q <sub>gs</sub>	$V_{DD} = 520V, I_{D} = 50A, V_{GS} = 10V$		38			
Gate-Drain Charge	Q <sub>gd</sub>			60			
Turn-on Delay Time	t <sub>d(on)</sub>			45			
Turn-on Rise Time	t <sub>r</sub>	V <sub>DD</sub> = 400V, I <sub>D</sub> = 50A,		161			
Turn-off Delay Time	t <sub>d(off)</sub>	$R_{\rm G} = 25\Omega$		287		ns	
Turn-off Fall Time	t <sub>f</sub>			87			
Drain-Source Body Diode Characte	eristics			·			
Body Diode Voltage	V <sub>SD</sub>	T <sub>J</sub> = 25°C, I <sub>SD</sub> = 72A, V <sub>GS</sub> = 0V		0.9	1.2	V	
Reverse Recovery Time	t <sub>rr</sub>			540		ns	
Reverse Recovery Charge	Q <sub>rr</sub>	V <sub>R</sub> = 400V, I <sub>F</sub> = 30A, di <sub>F</sub> /dt = 100A/µs		13.5		μC	
Peak Reverse Recovery Current	I <sub>rrm</sub>			50.4		Α	

#### Notes

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature
- 2.  $I_{AS}$  = 13.7A,  $V_{DD}$  = 50V,  $R_{G}$  = 25 $\Omega$ , Starting  $T_{J}$  = 25 $^{\circ}$ C
- 3. Identical low side and high side switch with identical  $R_G$

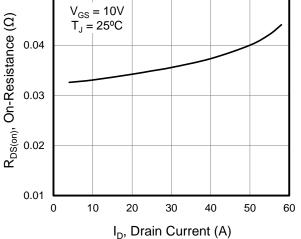


#### **Typical Characteristics** $T_J = 25^{\circ}C$ , unless otherwise noted

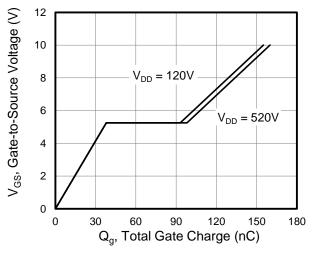


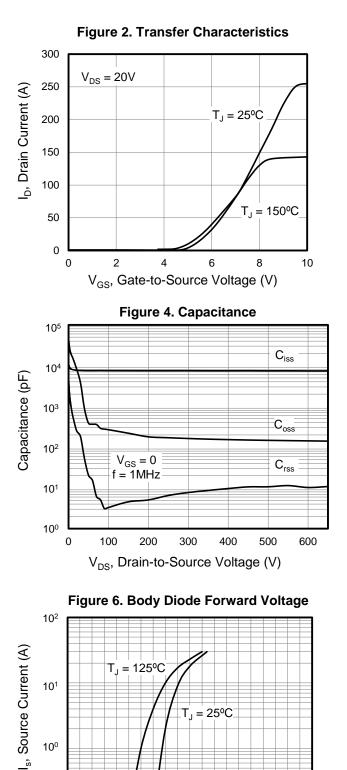
**Figure 1. Output Characteristics** 











1.5

2

10<sup>0</sup>

10-1

0

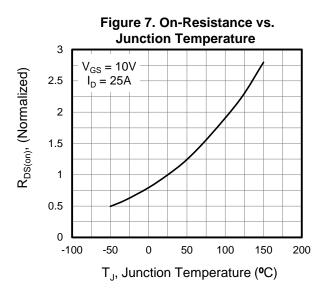
0.5

1

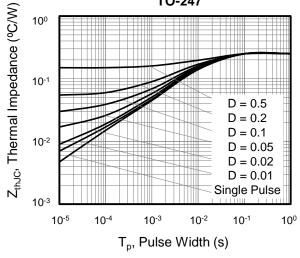
V<sub>SD</sub>, Source-to-Drain Voltage (V)

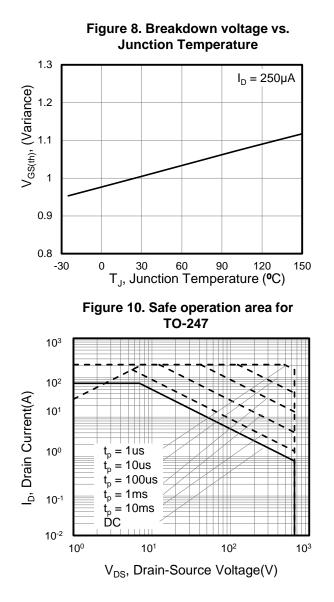


### **Typical Characteristics** $T_J = 25^{\circ}C$ , unless otherwise noted











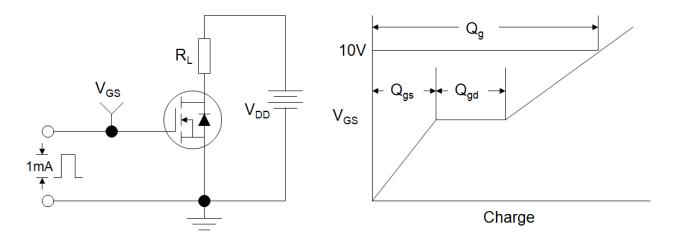


Figure B: Resistive Switching Test Circuit and Waveform

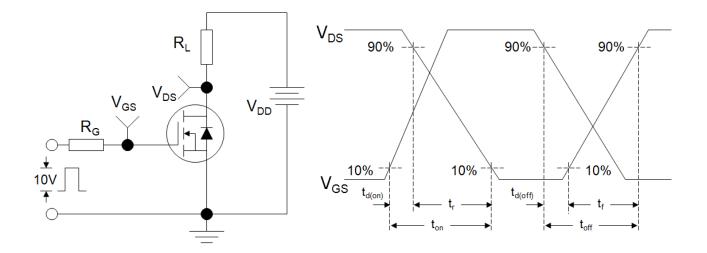
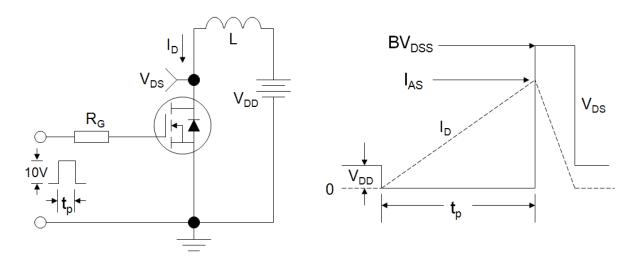
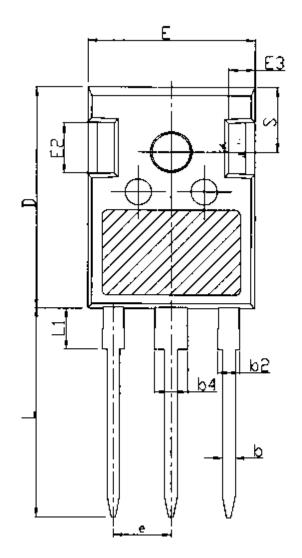


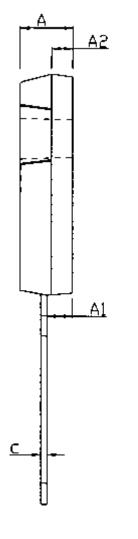
Figure C: Unclamped Inductive Switching Test Circuit and Waveform

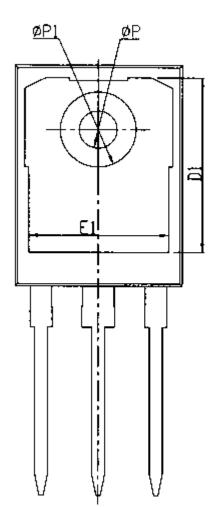


TO-247



t





Unit:mm					
Symbol	Min.	Nom	Max.		
А	4.80	5.00	5.20		
A1	2.21	2.41	2.61		
A2	1.85	2.00	2.15		
b	1.11	1.21	1.36		
b2	1.91	2.01	2.21		
b4	2.91	3.01	3.21		
с	0.51	0.61	0.75		
D	20.70	21.00	21.30		
D1	16.25	16.55	16.85		

Unit:mm				
Symbol	Min. Nom. M		Max.	
E	15.50	15.80	16.10	
E1	13.00	13.30	13.60	
E2	4.80	5.00	5.20	
E3	2.30	2.50	2.70	
е	5.44BSC			
L	19.62	19.92	20.22	
L1	-	-	4.30	
ΦΡ	3.40	3.60	3.80	
ΦΡ1	-	-	7.30	
S	6.15BSC			



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